Excited States and Valley Effects in a Negatively Charged Donor in a Si FinFET

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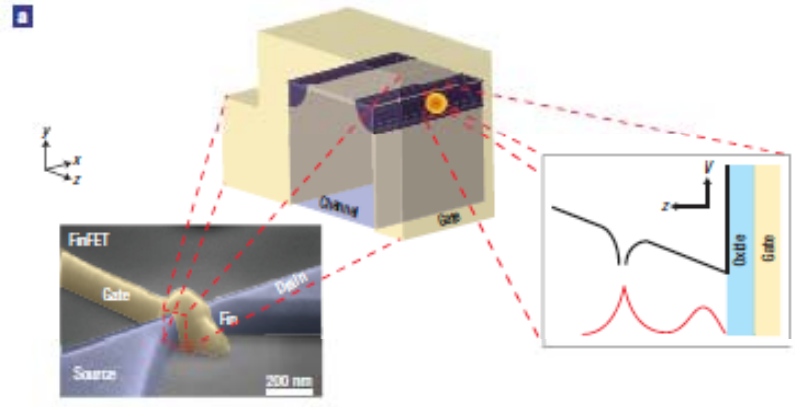
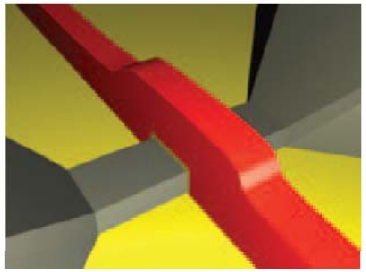
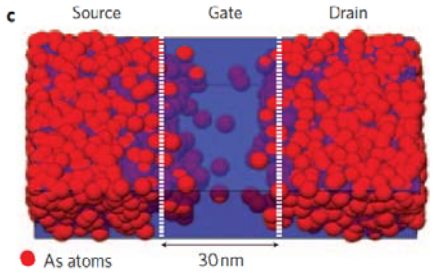
Single impurity devices in Si

- Top-down vs. Bottom-up
- Unintentional doping vs. controlled dopant implantation

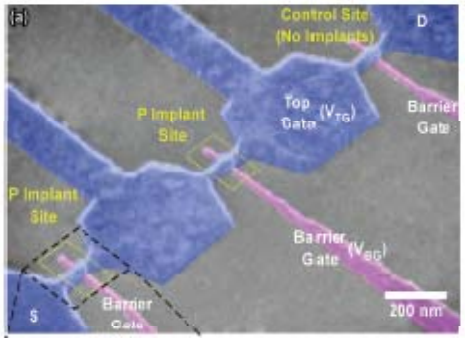


Rogge group, Nature Physics 4, 656 (2008)





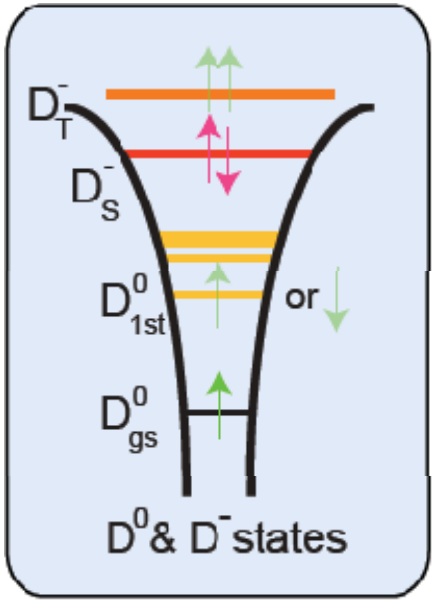
Sanquer group,
Nature Nanotechnology 5, 133 (2010)

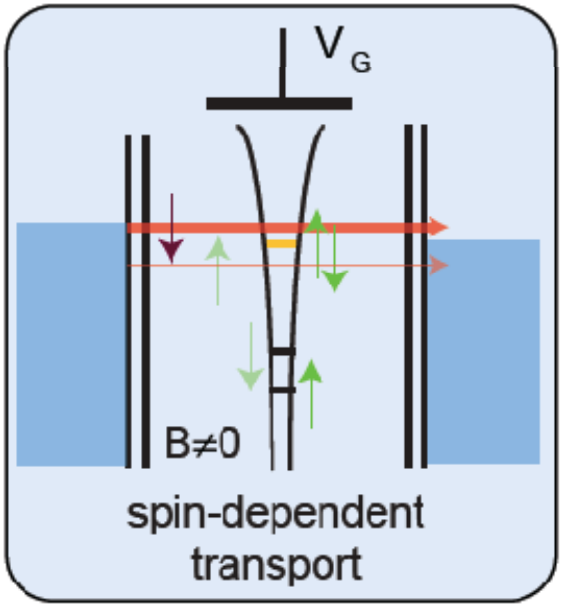


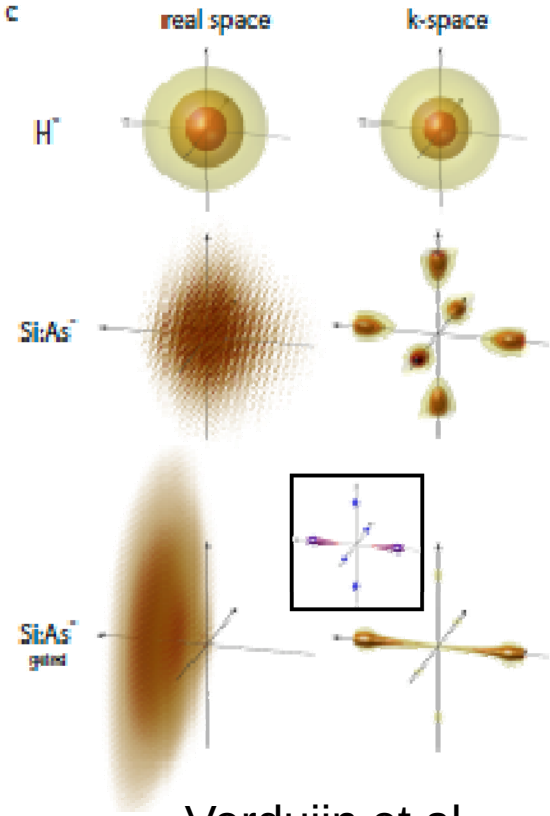
Dzurak group, Nano Lett. 10(1),11 (2010)

Why D- is important?

- 2e atomic system in silicon matrix (hydrogenic ion)
- pure atomic states (different from QD states)
- lab for studying momentum space contributions to few electron atomic physics
- known valley-orbit splitting
- Spin dependent tunneling for spin measurement
- Spin dependent relaxation (Lifetime enhanced transport)



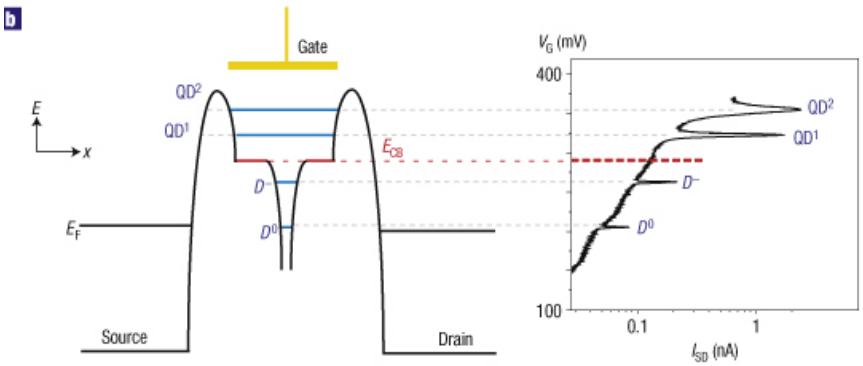


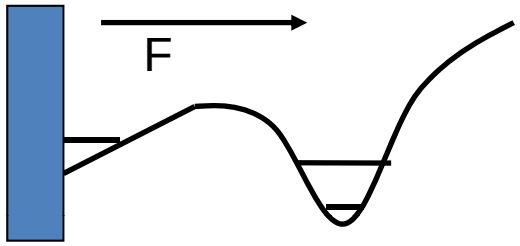


Verduijn et al.

Outline of results

Experiment: Transport spectroscopy in donor-interface well
Theory: Atomistic tight binding + SCF Hartree Fock (over 1M atoms)





Barrier-Si-impurity

Previously known facts about D-:

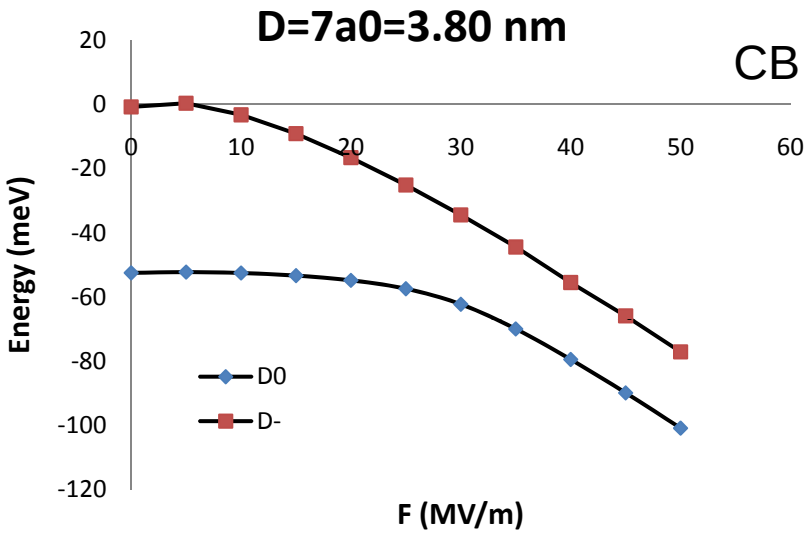
- Bulk measurements show only 1 bound singlet.
- P donor D- at -1.7 meV, As D- at -2 meV (bulk case).

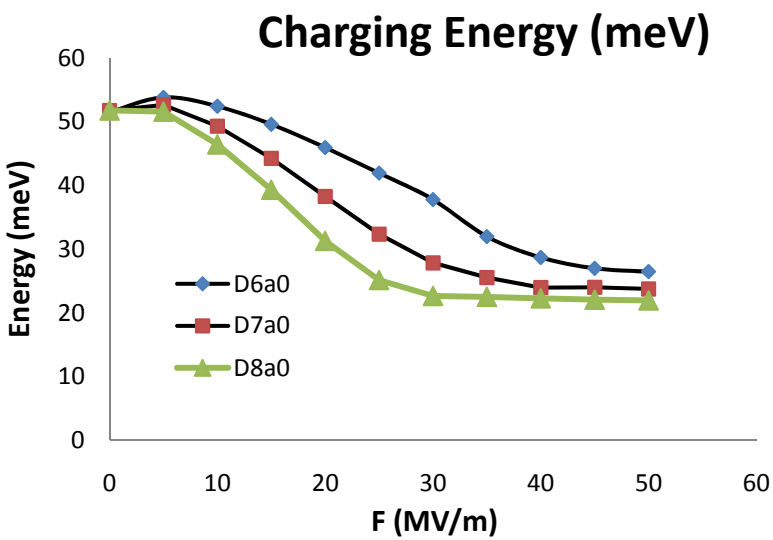
Results from this work:

1. Quantum confinement affects charging energy
2. Excited bound D- states observed including triplets at large E-fields
3. Valley dependence of exchange
4. Lifetime Enhanced Transport

Lansbergen, Rahman, Verduijn, Klimeck, Hollenberg, Rogge, arXiv 1008.1381 (2010)

D- charging energy from SCF TB



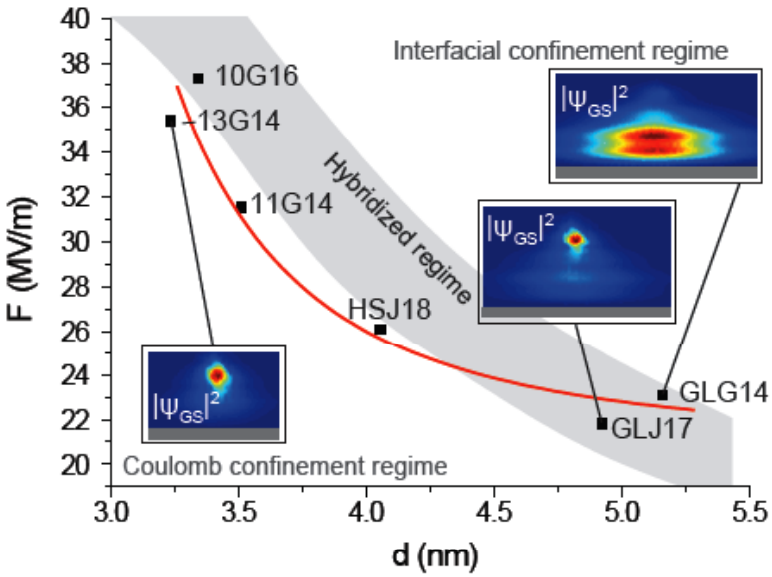


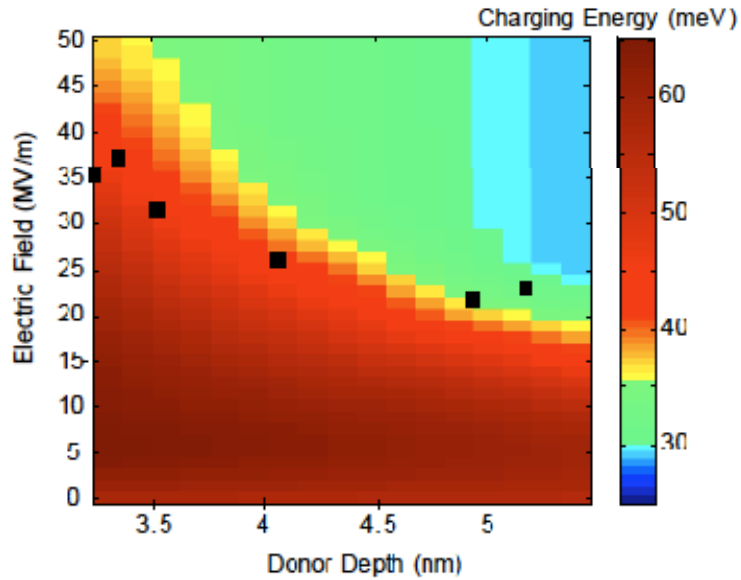
- Bulk P charging energy (CE) from SCF TB: 42.4 meV
- Known value from optical measurements: 43.9 meV

- CE depends on wf localization between interface well and donor well

- Other factors: Corner confinement, dielectric mismatch

D- charging energy (TB vs experiment)

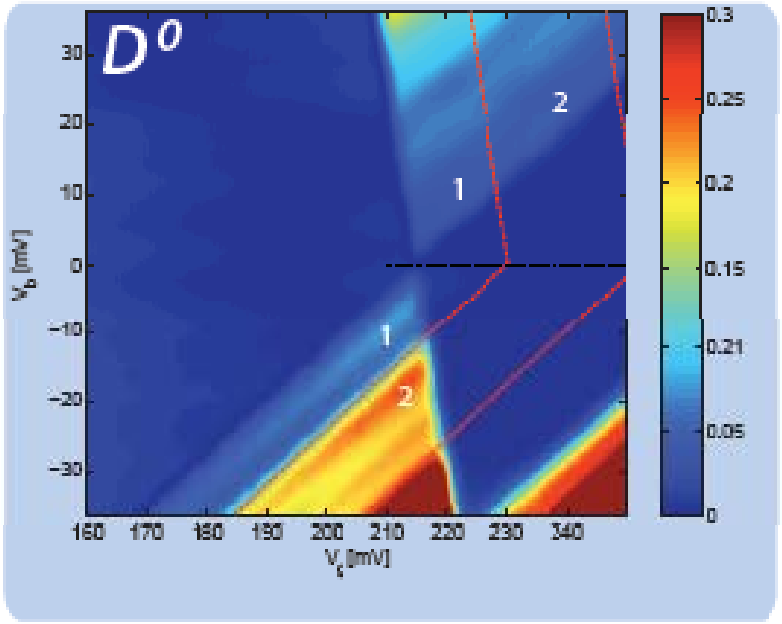


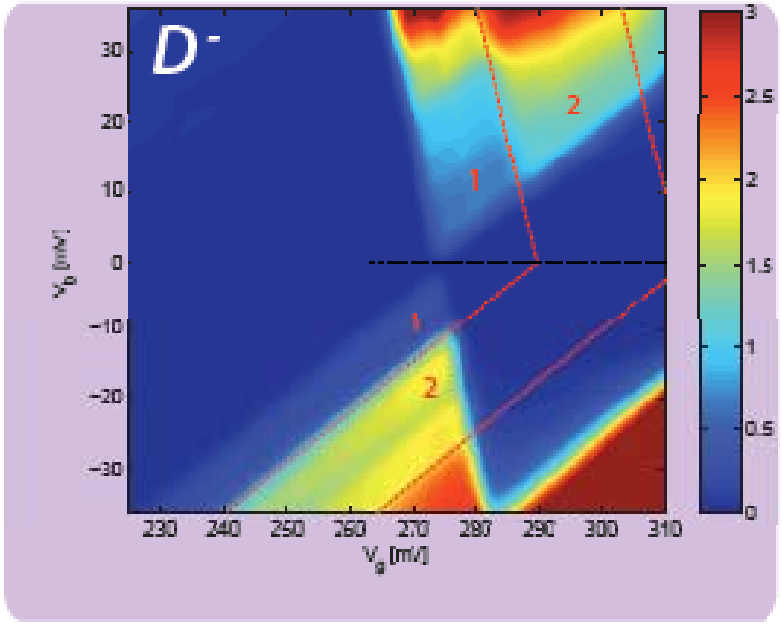


- Donor depths and fields known for 6 devices (previous work on D0 excited state spectroscopy)
- CE calculated for the same devices and compared to measurements
- Agreement within 5 meV, expected trends
- Sources of error: 1.5 meV accuracy, dielectric screening

Lansbergen, Rahman, Klimeck, Hollenberg, Rogge, Nature Physics 4, 656 (2008)

Bound excited states of D-





Bound excited D- states observed for the first time.

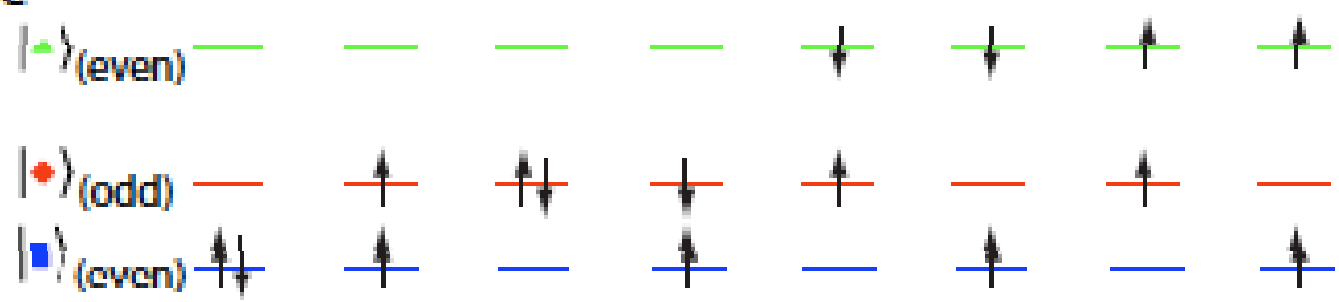
Excited manifold has triplet states also.

Theoretical prediction of D- excited states

b

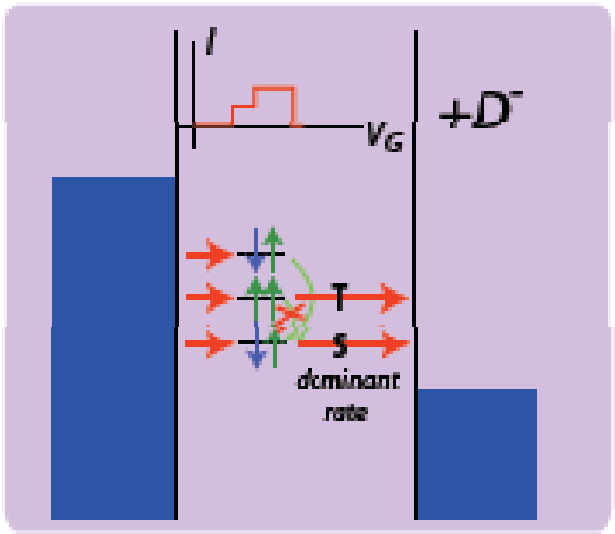
lower manifold	ΔE [meV]		higher manifold	ΔE [meV]	
wave function	theo.	exp.	wave function	theo.	exp.
$[\lvert\blacksquare\rangle\lvert\blacksquare\rangle\lvert S\rangle$	0	0	$[\lvert\blacktriangle\rangle\lvert\blacklozenge\rangle + \lvert\blacklozenge\rangle\lvert\blacktriangle\rangle]\lvert S\rangle$	7.9	
$[\lvert\blacklozenge\rangle\lvert\blacksquare\rangle - \lvert\blacksquare\rangle\lvert\blacklozenge\rangle]\lvert T\rangle$	1.5		$[\lvert\blacktriangle\rangle\lvert\blacksquare\rangle + \lvert\blacksquare\rangle\lvert\blacktriangle\rangle]\lvert S\rangle$	8.0	7.5
$[\lvert\blacklozenge\rangle\lvert\blacksquare\rangle + \lvert\blacksquare\rangle\lvert\blacklozenge\rangle]\lvert S\rangle$	1.6	1.0	$[\lvert\blacktriangle\rangle\lvert\blacklozenge\rangle - \lvert\blacklozenge\rangle\lvert\blacktriangle\rangle]\lvert T\rangle$	8.1	
$[\lvert\blacklozenge\rangle\lvert\blacklozenge\rangle\lvert S\rangle$	1.7		$[\lvert\blacktriangle\rangle\lvert\blacksquare\rangle - \lvert\blacksquare\rangle\lvert\blacktriangle\rangle]\lvert T\rangle$	11.2	10-15

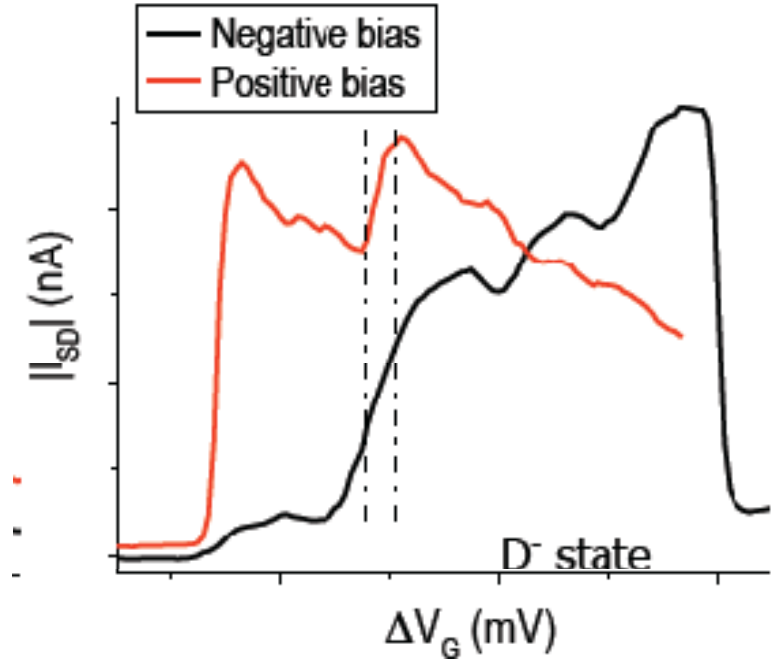
c



Electronic configurations across orthogonal valley states result in small exchange splitting

Lifetime enhanced transport in D-





- in the slow unloading direction only the ground state should be visible (asym. 1/2000)
- one of the states (steep step) in the excited manifold does not relax
- stronger coupling of this states leads to current step
- stronger coupling without LET can not lead to this step

Conclusions

- Quantitative description of the D- charging energy for 6 device samples
- Observation of bound D- excited states for the first time
- Qualitative agreement of excited state energies and spin symmetries
- Vanishing exchange splitting in the orthogonal valley states
- Observation of lifetime enhanced transport through D- excited states